

AMENDMENTS TO THE CLAIMS:

1. (Original) An integrated oxide removal and processing system,
comprising:

a process module operable to intentionally add at least one film layer to a
single semiconductor wafer; and

a transfer chamber module used to align the semiconductor wafer for the
process module, the transfer chamber module operable to expose the
semiconductor wafer to a vaporous solution, the vaporous solution substantially
inert with respect to the semiconductor wafer and operable to remove an
interfacial oxide layer therefrom prior to or after the intentional addition of the at
least one film layer.

2. (Original) The system of claim 1, wherein the semiconductor wafer
comprises silicon.

3. (Original) The system of claim 1, wherein the oxide layer is a chemical
oxide.

4. (Original) The system of claim 1, wherein the transfer chamber module
comprises one of the group consisting of a synthetic resinous fluorine-containing
polymer, polytetrafluoroethylene coating, and silicon carbide.

5. (Original) The system of claim 1, wherein the at least one film layer comprises one of the group consisting of SiO₂, epitaxial Si, polysilicon, and nitride.

6. (Original) The system of claim 1, wherein the vaporous solution comprises HF.

7. (Original) The system of claim 1, wherein the vaporous solution comprises .049% to 49% HF.

8. (Original) An integrated oxide removal and transfer chamber, comprising:

- a chamber operable to hold and align a single semiconductor wafer for presentation to a process module;

- a wafer support enclosed within the chamber; and

- a plurality of outlets operable to discharge an amount of a vaporous solution into the chamber, the vaporous solution substantially inert with respect to the wafer support and the semiconductor wafer and operable to remove an oxide layer from at least one surface of the semiconductor wafer.

9. (Original) The integrated oxide removal and transfer chamber of claim 8, wherein the chamber comprises one of the group consisting of a synthetic resinous fluorine-containing polymer, polytetrafluoroethylene coating, and silicon carbide.

10. (Original) The integrated oxide removal and transfer chamber of claim 8, wherein the semiconductor wafer comprises silicon.

11. (Original) The integrated oxide removal and transfer chamber of claim 8, wherein the wafer support is rotatable.

12. (Original) The integrated oxide removal and transfer chamber of claim 8, wherein the vaporous solution comprises HF.

13. (Original) The integrated oxide removal and transfer chamber of claim 8, wherein the vaporous solution comprises .049% to 49% HF.